

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI AVD0.5P** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	300 mA
V_{CE}	20 V
P_{DISS}	--- W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	35.0 °C/W

PACKAGE STYLE .280 4L PILL

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.220 / 5.59	.230 / 5.84
B		1.055 / 26.80
C	.275 / 6.99	.285 / 7.24
D	.004 / 0.10	.006 / 0.15
E	.050 / 1.27	.060 / 1.52
F	.118 / 3.00	.130 / 3.30

ORDER CODE: ASI10551

CHARACTERISTICS $T_c = 25\text{ }^\circ\text{C}$

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	I _C = 1 mA	50			V
BV_{CEO}	I _C = 5 mA	20			V
BV_{EBO}	I _E = 1 mA	3.5			V
I_{CES}	V _{CE} = 28 V			1.0	mA
h_{FE}	V _{CE} = 5.0 V I _C = 100 mA	15		120	---
P_G	V _{CC} = 12.5 V P _{OUT} = 0.5 W f = 1025 - 1150 MHz	10			dB